

IN THE ABSTRACT OF THE DISCLOSURE:

Please delete the present Abstract of the Disclosure and replace it with the following new Abstract of the Disclosure:

A method for fabricating a flash memory includes forming a tunnel oxide layer by depositing a material with a conduction band energy level lower than that of SiO<sub>2</sub> on a semiconductor substrate; forming a floating gate by depositing polysilicon on the tunnel oxide layer; forming an intergate dielectric layer on the floating gate; forming a control gate on the intergate dielectric layer; forming a gate electrode by patterning the tunnel oxide layer, the floating gate, the intergate dielectric layer and the control gate; and forming a source/drain region by implanting impurities into the substrate using the gate electrode as a mask.